

Applic. No.: 10/815,407
Amtd. Dated September 30, 2005
Reply to Office action of July 28, 2005

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of claims:

Claim 1 (currently amended). A semiconductor structure, comprising:

a substrate;

at least one component structure applied to said substrate and having at least one crack formed therein; and

a protective layer applied on said at least one component structure; and

a repair layer having a repair material filling said crack, said repair layer being removed again before one of further layers being applied and before subsequent processes being carried out, said repair layer having a thickness significantly less than a thickness of said protective layer.

Claim 2 (cancelled).

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Claim 3 (original). The semiconductor structure according to claim 1, wherein said repair layer is formed from a same material as a material of said protective layer.

Claim 4 (original). The semiconductor structure according to claim 1, wherein said repair layer is formed from a different material as a material of said protective layer.

Claim 5 (original). The semiconductor structure according to claim 1, wherein said repair layer is removed by at least one etching process selected from the group consisting of an isotropic etching process, a wet-chemical etching process, a fixed-time etching process, and an etching process in which an end point is recorded, residues of said repair layer remaining in said crack.

Claim 6 (original). The semiconductor structure according to claim 1, wherein said repair layer is deposited by a conformal deposition process.

Claim 7 (currently amended). The semiconductor structure according to claim [[2]] 1, wherein said protective layer is formed from at least one layer selected from the group consisting of a silicon dioxide layer and a TEOS layer; and

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said repair layer is formed from at least one layer selected from the group consisting of a silicon dioxide layer and a TEOS layer.

Claim 8 (currently amended). The semiconductor structure according to claim 1, further comprising A semiconductor structure, comprising:

a substrate;

at least one component structure applied to said substrate and having at least one crack formed therein;

a repair layer having a repair material filling said crack, said repair layer being removed again before one of further layers being applied and before subsequent processes being carried out; and

spacer structures for protecting the semiconductor structure and for assisting in an implantation process, said spacer structures containing a material selected from the group consisting of silicon dioxide, TEOS, and nitride.

Claim 9 (currently amended). The semiconductor structure according to claim [[2]] 1, wherein said repair layer is

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applied immediately before performing a subsequent etching step for removing said protective layer.

Claim 10 (currently amended). The semiconductor structure according to claim [[2]] 1, wherein said repair layer has a thickness less than one-third of a thickness of said protective layer.

Claim 11 (original). The semiconductor structure according to claim 1, wherein said repair layer has a thickness half a maximum crack width.

Claim 12 (currently amended). The semiconductor structure according to claim [[2]] 1, wherein said repair layer is applied using a same process as said protective layer.

Claim 13 (currently amended). The semiconductor structure according to claim [[2]] 1, wherein said repair layer is applied using a different process than a process used for applying said protective layer.

Claim 14 (currently amended). The semiconductor structure according to claim [[2]] 1, wherein said protective layer is removed after said protective layer has been repaired and after the subsequent processes have been carried out with the

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aid of at least etching process selected from the group
consisting of an isotropic etching process, a wet-chemical
etching process, and a fixed-time etching process.